

Serial No. New Application

REMARKS

Claims 16, 39, and 43 have been amended to eliminate multiple dependencies and to make stylistic changes.

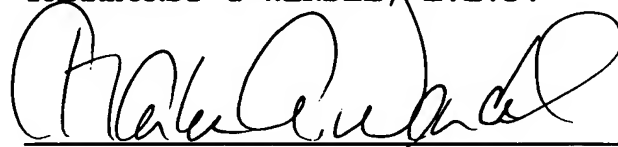
Claims 20 to 23, 27, 30, 31, 40, and 47 to 51 have been canceled. New claims 53 and 54 have been added directed to preferred embodiments of the invention.

Claims 1 to 19, 24 to 26, 28, 29, 32 to 39, 41 to 46, and 52 to 54 are presented for examination.

Examination of this application on its merits is respectfully requested.

Respectfully submitted,

PARKHURST & WENDEL, L.L.P.



Charles A. Wendel

Registration No. 24,453

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CAW/ch

Attorney Docket No. OGOH:108

PARKHURST & WENDEL, L.L.P.  
1421 Prince Street, Suite 210  
Alexandria, Virginia 22314-2805  
Telephone: (703) 739-0220

16(Amended). The method for fabricating an LDD thin film transistor in accordance with [any of claims] claim 1 [to 15, characterized in that] wherein, in the isolated resist-etching step, [is a both end-ashing step of removing at least] both end portions of the resist in the channel direction are removed by means of ashing with the use of a gas containing at least one of O<sub>2</sub> and ozone.

39.(Amended) The method of fabricating an LDD thin film transistor in accordance with claim 37 [or 38, characterized in that the reaction product film-forming step is a] , wherein a thermal oxide film [a thermal oxide film-forming step of forming the oxide films] as the reaction product film is formed by oxidizing the gate electrode material metal with heat.

43.(Amended) The method of fabricating an LDD thin film transistor in accordance with claim 41 [or 42 characterized in that the method includes] , wherein [a gate electrode material-selecting step of selecting] the gate electrode is made of an Mo-W alloy having Mo content of 15 -- 50 atom% [as a material of the gate electrode].